

ABSTRACT OF THE DISCLOSURE

A method for reading a bit of a memory cell in a non-volatile memory (NVM) cell array, the method comprising providing a memory cell comprising a bit to be read and at least one other bit not to be read, and reading the bit to be read with respect to a multi-bit reference cell, the reference cell comprising a first bit at a first non-ground programmed state and a second bit at a second non-ground programmed state. Compared with the prior art, the present invention may enable achieving the same sensing accuracy with improved read disturb immunity.